Ordering number:ENN2310A

Monolithic Linear IC

LA7311

VCR-Use PAL/SECAM Discriminator S-VHS Discriminator

Overview

The LA7311 is a PAL/SECAM discriminator and S-VHS discriminator IC. When used as PAL/SECAM discriminator, the LA7311 is highly resistant to noise and is capable of providing high sensitive discrimination, because it uses the FM demodulation, peak detection method. Further, the LA7311 uses very few external parts, making the space-saving and low-cost discrimination block available, because it requires neither ceramic filter nor resonance coil. When used as S-VHS discriminator, the LA7311 is also capable of providing high sensitive discrimination.

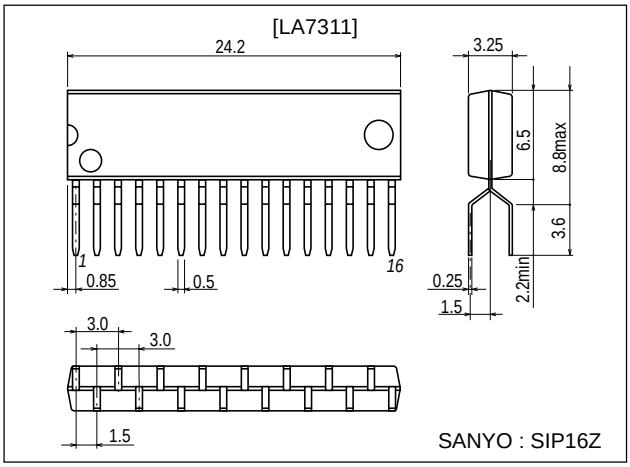
Features

- Highly resistant to noise and burst input level variations and capable of providing high sensitive discrimination.
- Fewer external parts required (Neither ceramic filter nor resonance coil required).
- On-chip display LED drivers.
- The polarity of burst gate pulse may be either positive or negative.

Package Dimensions

unit:mm

3193-SIP16Z



Specifications

Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V_{CC} max		7.0	V
Allowable power dissipation	Pd max		130	mW
Operating temperature	Topr		–10 to +70	˚C
Storage temperature	Tstg		–40 to +125	˚C

Operating Conditions at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage	V_{CC}		5.0	V
Operating voltage range	V_{CC} op		4.5 to 6.0	V

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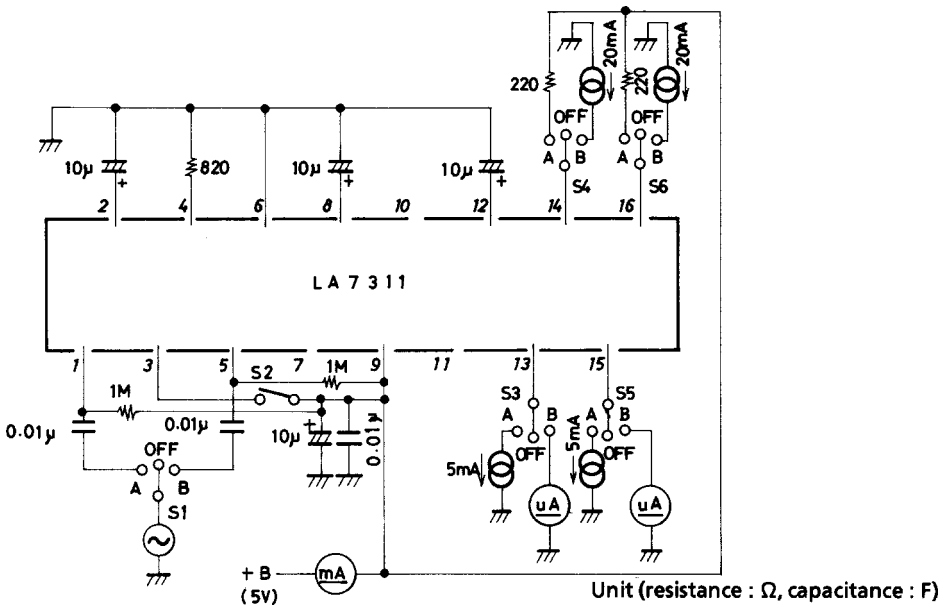
Operating Characteristics at Ta = 25˚C, V_{CC}=5V

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Current drain	I_{CC}		6.7	9.6	12.4	mA
F-V conversion gain (PB)	ΔV_P	Difference between output at 4.4MHz and output at 4.25MHz	75	105	135	mV
F-V conversion gain (REC)	ΔV_R	Difference between output at 4.4MHz and output at 4.25MHz	75	105	135	mV
PAL →SECAM inversion voltage difference	V_{8-12}		35	50	65	mV
R/P switching threshold voltage	V_{3TH}		2.0	2.35	2.7	V
BG Threshold voltage 1	V_{7TH}		1.5	1.7	1.9	V
BG Threshold voltage 2	V_{11TH}		3.2	3.4	3.6	V
Forced PAL threshold voltage	V_{10TH}		1.3	1.7	2.2	V
Forced SECAM threshold voltage	V_{2TH}		1.7	2.0	2.3	V
Discrimination output voltage 1	V_{13}	I_D=5mA	4.0	4.2	4.4	V
Discrimination output voltage 2	V_{15}	I_D=5mA	4.0	4.2	4.4	V
Discrimination output leakage current 1	$I_{13(leak)}$			0	5	µA
Discrimination output leakage current 2	$I_{15(leak)}$			0	5	µA
Pin 12 DC voltage	V_{12}	4.43MHz, 100mVp-p input	2.1	2.6	3.1	V
Input burst level	V_{IN}		60	100	200	mVp-p
Driver saturation voltage 1	V_{14}	I_D=20mA		170	400	mV
Driver saturation voltage 2	V_{16}	I_D=20mA		170	400	mV

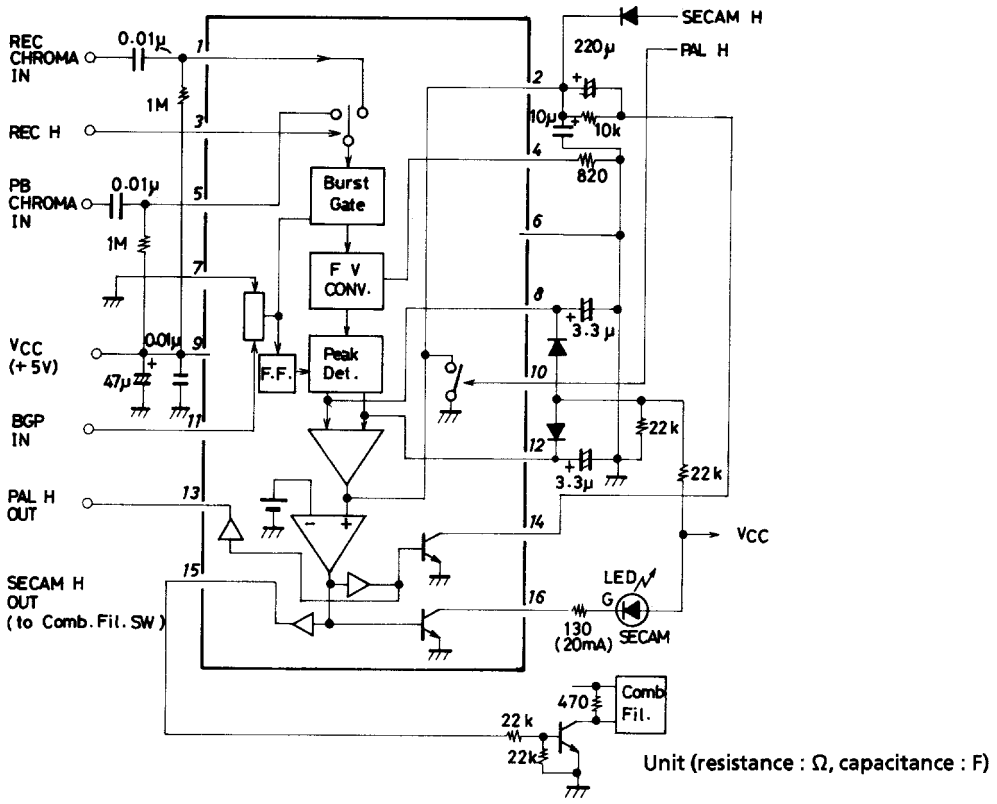
Test Circuit



Note : Remove the 1MΩ resistor connected across pins (1) and (9) and across pins (5) and (9) except when measuring ΔV_P, ΔV_R, V_{12}, V_{IN}.

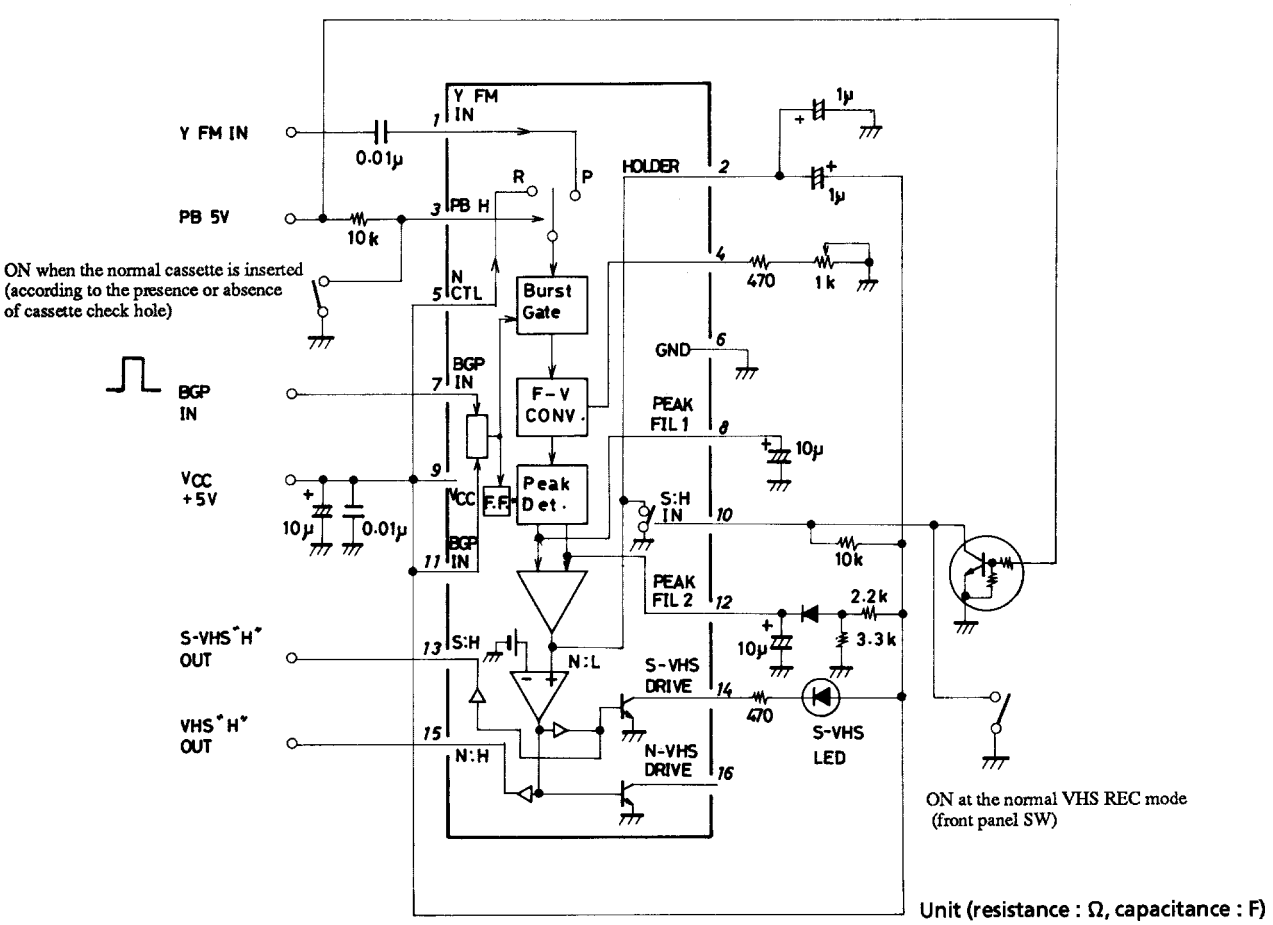
	S1	S2	S3	S4	S5	S6	Conditions
I_{CC}	off	off	off	off	off	off	V_9=5V
ΔV_P	B	↓	↓	↓	↓	↓	100mVp-p, difference between V_8 (or V_{12}) potential at 4.4MHz input and V_8 (or V_{12}) potential at 4.25MHz input
ΔV_R	A	on	↓	↓	↓	↓	100mVp-p, difference between V_8 (or V_{12}) potential at 4.4MHz input and V_8 (or V_{12}) potential at 4.25MHz input
$V_{8\text{-}12}$	off	off	↓	A	↓	↓	a (rise from 0) when V_7=0V, V_{11}=5V, V_8=1.9V, V_{12}=1.9V+a, V_{14}>4V
V_{3TH}	↓	↓	↓	off	↓	↓	V_3 (rise from 0) when V_1=V_7=V_{11}=0V, V_8=<0.1V
V_{7TH}	↓	↓	↓	↓	↓	↓	V_7 (rise from 0) when V_{11}=5V, V_8>1.0V
V_{11TH}	↓	↓	↓	↓	↓	↓	V_{11} (fall from 5V) when V_7=0V, V_8>1.0V
V_{10TH}	↓	↓	↓	↓	↓	A	V_{10} (rise from 0) when V_7=V_{11}=0V, V_{16}>4V
V_{2TH}	↓	↓	↓	A	↓	off	V_2 (rise from 0) when V_8=V_{12}=3V, V_{14}>4V
V_{13}	↓	↓	A	off	↓	↓	Pin 13 potential when V2=0V, drive current 5mA
V_{15}	↓	↓	off	↓	A	↓	Pin 15 potential when V_2=3V, drive current 5mA
$I_{13(leak)}$	↓	↓	B	↓	off	↓	V_2=3V, current which flows when pin 13 is connected to GND
$I_{15(leak)}$	↓	↓	off	↓	B	↓	V_2=0V, current which flows when pin 15 is connected to GND
$V_{14(sat)}$	↓	↓	↓	B	off	↓	Pin 14 potential when V_2=0V, drive current 20mA
$V_{16(sat)}$	↓	↓	↓	off	↓	B	Pin 6 potential when V_2=3V, drive current 20mA
V_{12}	A	on	↓	↓	↓	off	100mVp-p, 4.43MHz CW input, Apply 4μs BGP input to pin 11.
V_{IN}	A/B	on/off	↓	↓	↓	↓	

Equivalent Circuit Block Diagram and Sample Application Circuit (PAL/SECAM Discrimination)



Note 1 : When the BGP is positive, apply an input to pin 7 and connect pin 11 to V_{CC}.
Note 2 : When pin 10 is not in use, bring pin 10 to the open state or connect to GND.

Sample S-VHS Discriminator



Adjustment method : Adjust the VR (from VR center position) connected to pin 4 so that the DC voltage on pin 8 becomes 2.0V when the FM-Y signal at the (normal) VHS REC tape PB mode is input.

Note 1 : When the BGP is negative, apply an input to pin 11 and connect pin 7 to GND.

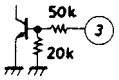
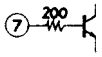
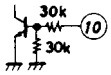
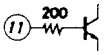
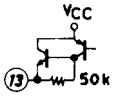
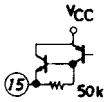
Note 2 : Pin 5 may be connected to GND.

Mode	Type of Cassette	Panel SW	V_{10}	V_2	Display
REC	N	S	H	L	S
		N	L	H	N
	S	S	H	L	S
		N	L	H	N
PB	N	S	L	H	N
		N	L	H	N
	S	S	L	Automatic discrimination	
		N	L	Automatic discrimination	

N ; NORMAL VHS, S ; S-VHS

Input/Output Configuration

Unit (resistance : Ω)

Pin	Pin Name	I/O Impedance or I/O Configuration		DC Voltage	Remarks
1	REC CHROMA IN	10kΩ		4.1V	
2	SECAM HOLDER				SECAM at 2.0V or greater
3	R/P CONTROL			0V (PB mode)	REC at 2.4V or greater
4	CURRENT SOURCE	Open emitter		410mV	
5	PB CHROMA IN	10kΩ		4.1V	
6	GND			0V	
7	BGP IN	Base			Burst gate at 1.7V or greater
8	PEAK FILTER 1	Emitter follower			
9	V_{CC}			5V	
10	PAL HIGH IN			0V	Forced PAL at 1.7V or greater
11	$\overline{\text{BGP}}$ IN	Base			Burst gate at 3.4V or less
12	PEAK FILTER 2	Emitter follower			
13	PAL HIGH OUT			4.1V (PAL mode)	Up to 5mA
14	PAL DRIVE	NPN open collector			Up to 25mA
15	SECAM HIGH OUT			4.1V (SECAM mode)	Up to 5mA
16	SECAM DRIVE	NPN open collector			Up to 25mA